

B5819W SCHOTTKY BARRIER DIODE

FEATURES

Power dissipation

P_D : 450 mW ($T_{amb}=25^\circ\text{C}$)

Collector current

I_F : 1 A

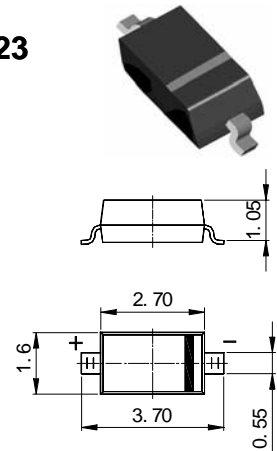
Collector-base voltage

V_R : 40 V

Operating and storage junction temperature range

T_J, T_{stg} : -55°C to $+150^\circ\text{C}$

SOD-123



Unit: mm

MARKING: SL

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^\circ\text{C}$ unless otherwise specified)

| Parameter | Symbol | Test conditions | MIN | MAX | UNIT |
|---------------------------------|------------|---|-----|--------------------|------|
| Reverse breakdown voltage | $V_{(BR)}$ | $I_R=1\text{mA}$ | 40 | | V |
| Reverse voltage leakage current | I_R | $V_R=40\text{V}$ $V_R=4\text{V}$ $V_R=6\text{V}$ | | 1 0.05 0.075 | mA |
| Forward voltage | V_F | $I_F=0.1\text{A}$ $I_F=1\text{A}$ $I_F=3\text{A}$ | | 0.45 0.6 0.9 | V |
| Diode capacitance | C_D | $V_R=4\text{V}, f=1\text{MHz}$ | | 120 | pF |